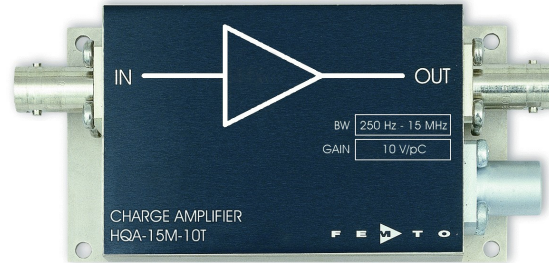




Preliminary Datasheet

HQA-15M-10T

High Frequency Charge Amplifier



Features	<ul style="list-style-type: none"> • High Gain of 10 V/pC • Wide Operating Range from 250 Hz to 15 MHz • Low Input Noise of 40×10^{-21} C/$\sqrt{\text{Hz}}$ and 700 pV/$\sqrt{\text{Hz}}$ • Optimized for Sinusoidal Signals from AC Coupled Charge Sources 																																																																			
Applications	<ul style="list-style-type: none"> • Pyro- and Piezoelectric Detectors • Tuning Fork Quartz Crystals • Length Extension Resonators • Atomic Force Microscopy • Optical Measurements • Charged Particle Beam Monitoring 																																																																			
Specifications	<p><i>Test Conditions</i> $V_s = \pm 15 \text{ V}, T_a = 25^\circ\text{C}$</p> <table border="0" style="width: 100%;"> <tr> <td style="width: 20%; vertical-align: top;">Gain</td> <td style="width: 50%;">Charge Gain</td> <td style="width: 30%;">10¹³ V/C</td> </tr> <tr> <td></td> <td>Equivalent Current Gain</td> <td>1.6 x 10⁶ V/A (@ 1 MHz sinusoidal input signal)</td> </tr> <tr> <td></td> <td>Gain Accuracy</td> <td>± 3 %</td> </tr> <tr> <td style="vertical-align: top;">Bandwidth</td> <td>Lower Cut-Off Frequency (-3 dB)</td> <td>250 Hz</td> </tr> <tr> <td></td> <td>Upper Cut-Off Frequency (-3 dB)</td> <td>15 MHz (with max. 100 pF source capacitance)</td> </tr> <tr> <td style="vertical-align: top;">Input</td> <td>Input Impedance</td> <td>1 GΩ // 10 nF</td> </tr> <tr> <td></td> <td>Effective AC Input Impedance</td> <td>20 Ω @ 1MHz</td> </tr> <tr> <td></td> <td>Input Charge Noise</td> <td>40 x 10⁻²¹ C/$\sqrt{\text{Hz}}$ (with open input)</td> </tr> <tr> <td></td> <td></td> <td>90 x 10⁻²¹ C/$\sqrt{\text{Hz}}$ (with 100 pF source capacitance)</td> </tr> <tr> <td></td> <td>Equivalent Input Current Noise</td> <td>250 fA/$\sqrt{\text{Hz}}$ (with open input)</td> </tr> <tr> <td></td> <td>(@ 1 MHz sinusoidal input signal)</td> <td>570 fA/$\sqrt{\text{Hz}}$ (with 100 pF source capacitance)</td> </tr> <tr> <td></td> <td>Input Voltage Noise</td> <td>700 pV/$\sqrt{\text{Hz}}$ (@ 1 MHz)</td> </tr> <tr> <td></td> <td>Max. Input Charge</td> <td>1 pC peak-peak</td> </tr> <tr> <td style="vertical-align: top;">Output</td> <td>Output Voltage Range</td> <td>10 V peak-peak (@ $\geq 1 \text{ M}\Omega$ load, for linear operation)</td> </tr> <tr> <td></td> <td>Output Impedance</td> <td>50 Ω (terminate with $\geq 1 \text{ M}\Omega$ load for best performance)</td> </tr> <tr> <td></td> <td>Integrated Broadband Noise</td> <td>typ. 20 mV peak-peak or 3.5 mV rms (@ $\geq 1 \text{ M}\Omega$ load)</td> </tr> <tr> <td style="vertical-align: top;">Power Supply</td> <td>Supply Voltage</td> <td>± 15 V</td> </tr> <tr> <td></td> <td>Supply Current</td> <td>± 35 mA typ. (depends on operating conditions, recommended power supply capability min. ± 100 mA)</td> </tr> <tr> <td style="vertical-align: top;">Case</td> <td>Weight</td> <td>200 g (0.44 lb.)</td> </tr> <tr> <td></td> <td>Material</td> <td>AlMg4.5Mn, nickel-plated</td> </tr> <tr> <td style="vertical-align: top;">Temperature Range</td> <td>Storage Temperature</td> <td>- 40 °C to +100 °C</td> </tr> <tr> <td></td> <td>Operating Temperature</td> <td>+20 °C to +40 °C</td> </tr> </table>		Gain	Charge Gain	10 ¹³ V/C		Equivalent Current Gain	1.6 x 10 ⁶ V/A (@ 1 MHz sinusoidal input signal)		Gain Accuracy	± 3 %	Bandwidth	Lower Cut-Off Frequency (-3 dB)	250 Hz		Upper Cut-Off Frequency (-3 dB)	15 MHz (with max. 100 pF source capacitance)	Input	Input Impedance	1 G Ω // 10 nF		Effective AC Input Impedance	20 Ω @ 1MHz		Input Charge Noise	40 x 10 ⁻²¹ C/ $\sqrt{\text{Hz}}$ (with open input)			90 x 10 ⁻²¹ C/ $\sqrt{\text{Hz}}$ (with 100 pF source capacitance)		Equivalent Input Current Noise	250 fA/ $\sqrt{\text{Hz}}$ (with open input)		(@ 1 MHz sinusoidal input signal)	570 fA/ $\sqrt{\text{Hz}}$ (with 100 pF source capacitance)		Input Voltage Noise	700 pV/ $\sqrt{\text{Hz}}$ (@ 1 MHz)		Max. Input Charge	1 pC peak-peak	Output	Output Voltage Range	10 V peak-peak (@ $\geq 1 \text{ M}\Omega$ load, for linear operation)		Output Impedance	50 Ω (terminate with $\geq 1 \text{ M}\Omega$ load for best performance)		Integrated Broadband Noise	typ. 20 mV peak-peak or 3.5 mV rms (@ $\geq 1 \text{ M}\Omega$ load)	Power Supply	Supply Voltage	± 15 V		Supply Current	± 35 mA typ. (depends on operating conditions, recommended power supply capability min. ± 100 mA)	Case	Weight	200 g (0.44 lb.)		Material	AlMg4.5Mn, nickel-plated	Temperature Range	Storage Temperature	- 40 °C to +100 °C		Operating Temperature	+20 °C to +40 °C
Gain	Charge Gain	10 ¹³ V/C																																																																		
	Equivalent Current Gain	1.6 x 10 ⁶ V/A (@ 1 MHz sinusoidal input signal)																																																																		
	Gain Accuracy	± 3 %																																																																		
Bandwidth	Lower Cut-Off Frequency (-3 dB)	250 Hz																																																																		
	Upper Cut-Off Frequency (-3 dB)	15 MHz (with max. 100 pF source capacitance)																																																																		
Input	Input Impedance	1 G Ω // 10 nF																																																																		
	Effective AC Input Impedance	20 Ω @ 1MHz																																																																		
	Input Charge Noise	40 x 10 ⁻²¹ C/ $\sqrt{\text{Hz}}$ (with open input)																																																																		
		90 x 10 ⁻²¹ C/ $\sqrt{\text{Hz}}$ (with 100 pF source capacitance)																																																																		
	Equivalent Input Current Noise	250 fA/ $\sqrt{\text{Hz}}$ (with open input)																																																																		
	(@ 1 MHz sinusoidal input signal)	570 fA/ $\sqrt{\text{Hz}}$ (with 100 pF source capacitance)																																																																		
	Input Voltage Noise	700 pV/ $\sqrt{\text{Hz}}$ (@ 1 MHz)																																																																		
	Max. Input Charge	1 pC peak-peak																																																																		
Output	Output Voltage Range	10 V peak-peak (@ $\geq 1 \text{ M}\Omega$ load, for linear operation)																																																																		
	Output Impedance	50 Ω (terminate with $\geq 1 \text{ M}\Omega$ load for best performance)																																																																		
	Integrated Broadband Noise	typ. 20 mV peak-peak or 3.5 mV rms (@ $\geq 1 \text{ M}\Omega$ load)																																																																		
Power Supply	Supply Voltage	± 15 V																																																																		
	Supply Current	± 35 mA typ. (depends on operating conditions, recommended power supply capability min. ± 100 mA)																																																																		
Case	Weight	200 g (0.44 lb.)																																																																		
	Material	AlMg4.5Mn, nickel-plated																																																																		
Temperature Range	Storage Temperature	- 40 °C to +100 °C																																																																		
	Operating Temperature	+20 °C to +40 °C																																																																		

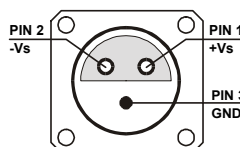
High Frequency Charge Amplifier

Absolute Maximum Ratings

Input Voltage 20 V peak-peak
 Power Supply Voltage ± 18 V

Connectors

Input BNC
 Output BNC
 Power Supply LEMO series 1S, 3-pin fixed socket
 Pin 1: + 15V
 Pin 2: - 15V
 Pin 3: GND

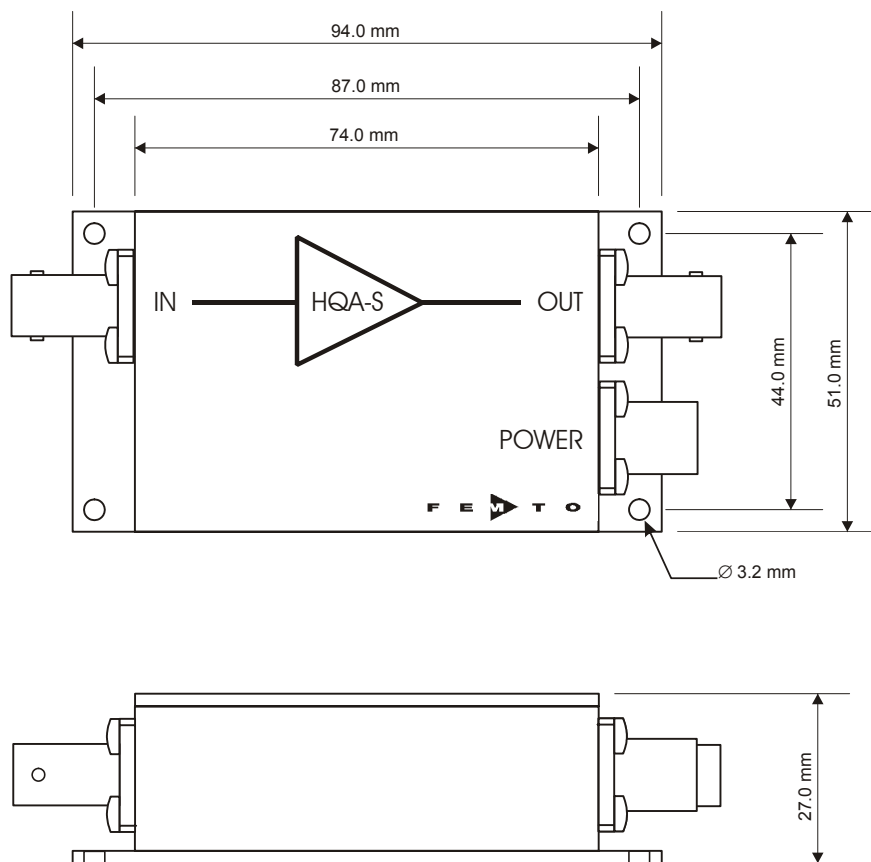


Operation

General:
 The amplifier is AC coupled for direct use with a charge sensor producing sinusoidal signals with no DC background. A source capacitance of less than 1 nF is recommended for proper operation. If the effective source capacitance (sensor plus cable capacitance) is small relative to the effective input impedance of the amplifier (10 nF) the amplifier acts as a virtual ground and most of the charge flows into the amplifier input. At 1 MHz the amplifier input capacitance of 10 nF corresponds to a complex input impedance of 20 Ω . An input resistor of 1 G Ω is incorporated to prevent buildup of static charge. The amplifier is not suited for sources producing an average DC background current as this would saturate the device.

High Frequency Charge Amplifier

Dimensions



DZ01-2299001-R1

FEMTO Messtechnik GmbH
 Klosterstr. 64
 D-10179 Berlin · Germany
 Tel.: +49-(0)30-280 4711-0
 Fax: +49-(0)30-280 4711-11
 e-mail: info@femto.de
 http://www.femto.de

Specifications are subject to change without notice. Information furnished herein is believed to be accurate and reliable. However, no responsibility is assumed by FEMTO Messtechnik GmbH for its use, nor for any infringement of patents or other rights granted by implication or otherwise under any patent rights of FEMTO Messtechnik GmbH. Product names mentioned may also be trademarks used here for identification purposes only.
 © by FEMTO Messtechnik GmbH
 Printed in Germany